## PROCESSING OF $ZrB_2$ -ZrC- $Zr_xSi_y$ CERAMIC BY REACTIVE METAL

## PENETRATION

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by

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#### ABSTRACT

The processing of ZrB 2-ZrC-Zr<sub>x</sub>Si<sub>y</sub> composite by reactive metal penetration was investigated as a successor to the ZrB 2-SiC composites for hypersonic vehicles application, which cannot be used for extended time at temp eratures greater than 1600°C due to formation of SiO and CO gases. Zirconium (Zr), zirconium disilicide  $(ZrSi_2)$ , and boron carbide  $(B_4C)$  were reacted in graphite crucibles for 60, 120, 180, and 240 minutes. Microscopy and x -ray diffraction (XRD) deduced the formation of a heterogeneous microstructure of ZrB<sub>2</sub>-ZrC-Zr<sub>x</sub>Si<sub>y</sub> precipitates surrounded by a solidified Zr-Si melt. Unreacte d boron carbide was observed in samples held at 1860 °C for 60 thermodynamic equilibrium was not achieved minutes and 120 minutes, so . The reaction for the composite formation is as follows:

 $Zr+B_4C+ZrSi_2 \longrightarrow ZrB_2+ZrC+Zr_xSi_y$ 

The most consistent microstructures were seen on the samples heated for 180 minutes and 240 minutes, in which the free B <sub>4</sub>C completely decomposed to zirconium boride and carbide. Also, because of the closeness of the initial compositions of Zr and Si (12 wt% and 14 wt%) on the Zr-Si phase diagram, there was not much difference in the final phases obtained in both compositions.



## TABLE OF CONTENTS

ACKNOWLEDGEMENTSiv
ABSTRACTv
Chapter 1: INTRODUCTION1
1.1: Overview of Ultra-High Temperature Ceramics1
1.2: Research Objective2
Chapter 2: LITERATURE REVIEW4
2.1: Processing of Ultra-High Temperature Ceramics4
2.1.1: Reactive Metal Penetration4
2.2: Phase Diagrams
2.2.1: Zr-Si Phase Diagram6
2.2.2: B-C-Zr Phase Diagram9
2.2.3: Zr-B <sub>4</sub> C-ZrSi <sub>2</sub> Phase Diagram9
2.3: Oxidation of ultra-high temperature ceramic13
2.3.1 Zr-Si-O Phase Diagram13
2.3.2 $ZrO_2$ -SiO <sub>2</sub> Phase Diagram14
Chapter 3: RESEARCH METHODOLOGY17
3.1: Sample Preparation17
3.2: Experimental Procedure
3.3: Microstructure Characterization19
Chapter 4: RESULTS



4.3: Results Summary	.27
Chapter 5: DISCUSSION	.45
5.1: Oxygen Potential Reduction within the graphite Enclosure	.45
5.2: Phase Relations between Zr/B <sub>4</sub> C/Si	.45
5.4: Microstructures	.47
Chapter 6: CONCLUSION	.52
REFERENCES	.53
CURRICULUM VITA	.56



## LIST OF FIGURES

Figure 2.1: Ellingham Diagram for Carbides [Outotec]	7
Figure 2.2: Zr-Si Phase Diagram in mole fraction. The red arrows indicate the starting	
Zr-Si liquid compositions [Okamoto-1996].	8
Figure 2.3: B-C-Zr Ternary Phase Diagram at 1800°C [Outotec]1	0
Figure 2.4: B-C-Zr Ternary Phase Diagram at 2400°C [Outotec]1	1
Figure 2.5: Zr-B <sub>4</sub> C-ZrSi <sub>2</sub> Pseudo-Ternary Phase Diagram at 1860°C [FactSage]1	12
Figure 2.6: FEA model of the ZrB <sub>2</sub> -ZrC-Zr Composite with Oxide Scales [Petla-2010]. 1	4
Figure 2.7: Zr-Si-O Ternary Phase Diagram at 1680°C [Sorrell-1986]1	15
Figure 2.8: ZrO <sub>2</sub> -SiO <sub>2</sub> Pseudo-Binary Phase Diagram [Kaiser-2008]1	6
Figure 3.1: Sample Setup1	17
Figure 3.2: Graphite Enclosure Setup 2	20
Figure 3.3: Graphite Enclosure with Graphite Crucible Sample	21
Figure 3.4: Cross-section of the Graphite Enclosure2	22
Figure 3.5: Reaction Tube Setup 2	23
Figure 3.7: Reaction Tube Cap 2	24
Figure 3.8: Cooling Jacket 2	24
Figure 3.6: Quartz Reaction Tube2	24
Figure 3.9: Bottom Reaction Tube Cap2	25
Figure 3.10: Cooling Jacket Cap 2	25
Figure 4.1: Cross-section of a processed sample showing the effect of the levitation	
caused by the magnetic field of the induction furnace	28





ix

Figure 4.17: Micrograph with ZrB <sub>2</sub> -ZrC precipitates in a completely reacted sample he	əld
at 1860°C for 240 minutes	. 44
Figure 5.1: Ellingham Diagram for oxides.	. 48
Figure 5.2: Zr-B4C-Si Pseudo-Ternary Phase Diagram at 1900°C	. 49
Figure 5.3: Zr-B <sub>4</sub> C-Si Pseudo-Ternary Phase Diagram at 2400°C	. 50
Figure 5.4: Ellingham Diagram for Zirconium Silicides	. 51



#### **Chapter 1: INTRODUCTION**

#### 1.1: Overview of Ultra-High Temperature Ceramics

The wing leading edge and nose caps of the hypersonic vehicles are subject ed to temperatures greater than 2000°C during their reentry and sustain severe conditions caused by vaporization, erosion and oxidation. In addition to chemical reactivity, the durability of materials to ultrahigh temperatures (>1600°C) causes severe mechanical interaction resulting from thermal shock for ceramic mat erials as they cycle from room temperature to the extreme temperatures. The composites must then sustain a synergistic effect contributed from the chemical and mechanical interactions at ultrahigh temperatures exposure, requiring selection of the optimal material system.

The carbides and borides of the transition metals (e.g., ZrC, HfC, ZrB<sub>2</sub> and HfB<sub>2</sub>) have been suggested as materials for ultrahigh temperature ceramics [ Opeka-2004. Bronson-1992], because of their exceptionally high melting temperatures of greater than 3000°C. The other important distinctive qualities are solid-state stability, good thermomechanical properties, and high mechanical properties, values as shown in table 1.1. However, a scale must protect the foregoing carbides and borides, which readily react with oxvgen. Various researchers [Hinze-1975, Karlsdottir-2007, Fahrenholtz -2007, and Monteverde-2007] determined through their meticulous study that the ZrB 2-SiC system is protected from oxidation because an adherent silicate scale forms and decreases significantly the diffusion of oxygen into the substrate . However, the formation of SiO and CO limits the operational temperature of SiC because the CO forms along the SiC/ SiO<sub>2</sub> interface as well as SiO (g) creates a bubbling action at



temperatures greater than 1600 -1700°C [Levine-2002, Bronson -2008,]. Hence, a silicide must be found without the formation of gaseous products though still with the protective properties of a silicate layer, which lowers the oxygen diffusion.

An additional drawback of ultrahigh temperature materials is their processing because the systems require ultrahigh temperatures, controlled porosity and significantly low impurities. For example, ZrB<sub>2</sub> and ZrC have melting points of 3244°C [Okamoto-1993] and 3427°C [Okamoto-1996], respectively, but SiO <sub>2</sub> impurities coalescing in the grain boundaries would lower the yield strength. Johnson et al. [6] developed a technique of reacting liquid Zr with a packed bed of B<sub>4</sub>C, the process called reactive metal penetration. As the Zr penetrates the packed bed, the following reaction ensues exothermically with the Gibbs free energy of formation at 1855 °C,  $\Delta G = -673$ kJ:  $3Zr+B_4C \longrightarrow 2ZrB_2+ZrC$  (1.1)

An additional contribution would be to use a Zr -Si melt instead of Zr melt to create a boride/carbide precipitates emb edded in a Zr -Si alloy matrix. Upon oxidation, the Si would react to form a silicated layer.

#### 1.2: Research Objective

The research investigates the processing of a ceramic composite consisting of  $ZrB_2$ , ZrC,  $Zr_xSi_y$  precipitates within a metal matrix of  $Zr_-Si$  alloy. The objective of the research was to determine the extent of the silicide precipitation as the  $Zr_-Si$  liquid penetrates the B<sub>4</sub>C packed bed. The original Zr-Si liquid corresponded to the Zr-12 wt% Si, which lies within the Zr<sub>3</sub>Si-ZrSi two-phase region and Zr-16 wt% Si, which lies within the Zr<sub>3</sub>Si-ZrSi phase diagram. The Zr<sub>x</sub>Si<sub>y</sub> would ultimately f orm a



protective SiO<sub>2</sub> and ZrO<sub>2</sub> scales to provide oxidation resistance to the composite. The liquid SiO<sub>2</sub> embedded in the ZrO<sub>2</sub> scales fills up the cracks resulting in stress reduction. The study investigated the processing  $ZrB_2$ -ZrC- $Zr_xSi_y$  composite by reactive metal penetration and its dependence on time.

Material	Melting Temperature (°C)	Thermal Expansion Co-efficient (10 <sup>-6</sup> C <sup>-1</sup> )	Flexural Strength (MPa)	Young's Modulus (GPa)	Density ³ (g/cm)
ZrB <sub>2</sub>	3244	6.2	351	489	6.1
ZrC	3427	7.1	323	390	6.7
HfB <sub>2</sub>	3250	6.5	340	530	11.2
HfC	3890	7.1	150	424	12.7
SiC	2545	4	596	448	3.22

 Table 1.1: Properties of Borides and Carbides [Okamoto-1993, Okamoto-1996, Samsonov-1980]



#### Chapter 2: LITERATURE REVIEW

#### 2.1: Processing of Ultra-High Temperature Ceramics

There are several methods of processing ultra-high temperature ceramics (UHTC) though reactive metal penetration is an economical and uncomplicated technique of creating interconnecting precipitates in a metal/ceramic composite, without hot pressing . F or considering systems suitable for reactive metal penetration, the thermodynamic reactions and thermodynamic compatibility of phases must be determined [Fahrenholtz-2006]. The reactions should be thermodynamically favorable which refers to the Gibb's free energy of reaction, as shown in figure 2.1. The Gibbs free energy of ZrC is considerably less than  $B_4C$  and the liquid would displace the boron via the reaction shown in equation 1.1. The phase equilibria must then be checked with phase diagrams, if available.

#### 2.1.1: Reactive Metal Penetration

Tomsia et al. [5] and Johnson et al. [6] have used reactive metal penetration to form a composite by capitalizing on interfacial reaction between a metal and ceramic. Tomsia et al. [5] reacted molten aluminum with mullite to form  $Al_2O_3$  with Al-Si alloy. The liquid aluminum penetrated the silicate preform dissolving  $SiO_2$  and forming  $Al_2O_3$  at the reaction layer. The process continues with oxygen diffusing through the initial  $Al_2O_3$ product and reacting with molten aluminum forming more  $Al_2O_3$ . The dissolved Si moves away from the reaction zone forming Al-Si alloy.

 $3(Al_2O_3.2SiO_2) + (8+x)Al \longrightarrow 13Al_2O_3 + Al_xSi_y + (6-y)Si$  (2.1)



Similarly, Johnson et al. [6] reported that molten zirconium infiltrated through the open porosity of B  $_4$ C reacting to f orm simultaneously precipitates of ZrB  $_2$  and ZrC. The dissolution of B  $_4$ C re sults in a thin boron -rich zirconium alloy. The boron-rich zirconium alloy pulls down the previously formed ZrB  $_2$ -ZrC layer by transportation phenomena and at the same time, reacting to leave behind a ZrB $_2$ -ZrC-Zr composite. Liquid metal can infuse into a ceramic preform by creating a pressure difference between the outer wall and inner core as aluminum or zirconium penetrating the ceramic preforms of mullite (3Al  $_2O_3.2SiO_2$ ), SiO $_2$  or B $_4$ C [Bronson-1997]. For cera mics with low open porosity, Odegard and Bronson considered capillary motion driven by surface tension instead of pressure difference for transporting the liquid metal with the reaction shown in equation 1.1.

For the ZrB  $_2$ -ZrC-Zr<sub>x</sub>Si<sub>y</sub> system, with the addition of ZrSi  $_2$  to the initial constituents, the Zr serves as a carrier for Si when liquid Zr  $_-$ Si penetrates into a preform. Zirconium silicides form upon cooling and their composition depends  $_-$  on the initial zirconium and zirc  $_-$  onium disilicides. The reaction occurs very fast with linear kinetics with a rate constant between  $1.6 \times 10$   $_-^2$  and  $3.9 \times 10$   $_-^2$  cm<sup>2</sup>/s [ Tomsia-1999, Johnson-1991]. Initially, the rate  $_-$  determining step will be the interfacial reaction between Zr-Si melt and boron carbide. Once the reaction initiates, the boron carbide  $_-$  liquid Zr-Si reaction will be faster than the diffusion of Si, B and C [Johnson-1991, Lu-1999, Tomsia-1999, Fahrenholtz-2006,].

$$(3+x)Zr + B_4C + yZrSi_2 \longrightarrow 2ZrB_2 + ZrC + Zr_xSi_{2y}$$
(2.3)



#### 2.2: Phase Diagrams

#### 2.2.1: Zr-Si Phase Diagram

The Zr-Si phase diagram gives the phase equilibria with a maximum melting at 2250°C for Zr <sub>5</sub>Si<sub>4</sub> compound, as shown in figure 2.2. The melting temperatures of Si and Zr are 1414 °C and 1855 °C respectively. Eutectic reactions occur on either side of binary - at 1370°C in the Si-rich region (10 at% Zr) and at 1570°C in the Zr-rich region (91.2 at % Zr). The maximum solubility of Si in Zr is less than 1 at % Si (due to the relatively large size of Zr atom) forming Zr (body centered cubic, BCC) and Zr (hexagonal close packed, HCP), but Zr is not soluble in Si . The Zr -Si system has the following intermetallic compounds: ZrSi<sub>2</sub>, ZrSi and ZrSi, Zr<sub>5</sub>Si<sub>4</sub> and Zr<sub>5</sub>Si<sub>4</sub>, Zr<sub>3</sub>Si<sub>2</sub>, Zr<sub>5</sub>Si<sub>3</sub>, Zr<sub>2</sub>Si and Zr<sub>3</sub>Si. The ZrSi<sub>2</sub> (33 at% Zr) phase initially forms at 1620 °C with a peritectic transformation of liquid and ZrSi. Similarly, ZrSi forms from the peritectic reaction of liquid and Zr <sub>5</sub>Si<sub>4</sub> at 2210 °C though ZrSi structure changes at 1460 °C. Polymorphic transformations also occur at 1860 °C for Zr<sub>5</sub>Si<sub>4</sub> and Zr<sub>3</sub>Si<sub>2</sub>. The Zr <sub>5</sub>Si<sub>4</sub> undergoes a congruent transformation at 2210 °C. The peritectic formation of Zr <sub>3</sub>Si<sub>2</sub> (60 at% Zr) occurs at 2215°C. The Zr<sub>5</sub>Si<sub>3</sub> (62.5 at% Zr) also forms peritectically, but transforms with a eutectoid reaction at 1745 °C forming Zr<sub>2</sub>Si and Zr<sub>3</sub>Si<sub>2</sub> when cooled slowly. The Zr<sub>5</sub>Si<sub>3</sub> is thermodynamically unstable at temperatures less than 1745 ° C as indicated by the Zr-Si phase diagram. The incongruent reactions of Zr<sub>2</sub>Si and Zr<sub>3</sub>Si occur at 1925°C and 1650°C respectively.





Figure 2.1: Ellingham Diagram for Carbides [Outotec].





Figure 2.2: Zr-Si Phase Diagram in mole fraction. The red arrows indicate the starting Zr-Si liquid compositions [Okamoto-1996].

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Weight Percent Zirconium

#### 2.2.2: B-C-Zr Phase Diagram

Isothermal sections of Zr-B-C system at temperatures, 1800 °C and 2400 °C are shown in figures 2.3 and 2.4. For the isothermal section at 1800 °C, we observe four binary compounds, ZrB  $_2$ , ZrC, B  $_4$ C, and ZrB  $_{12}$ ; and the three -phase field , ZrB<sub>2</sub>+ZrC+LIQUID forms. The phase diagram shows no other liquid present apart from the unreacted molten zirconium. The three-phase field (ZrB<sub>2</sub>+ZrC+LIQUID) is a product of molten Zr reacting with B<sub>4</sub>C. Phase layers such as ZrC+B<sub>4</sub>C and ZrC+B<sub>4</sub>C+C are also present at 1800 °C. At 2400 °C, boron-rich liquid exists due to the peritectic melting of ZrB<sub>12</sub> at 2030 °C and eutectic reaction between ZrB<sub>2</sub>, B<sub>4</sub>C, and C at 2165 °C. The Zr-rich liquid region grows larger at 2400 °C due to the d ecomposition of some of the ZrB<sub>2</sub>+ZrC+LIQUID phase.

#### 2.2.3: Zr-B<sub>4</sub>C-ZrSi<sub>2</sub> Phase Diagram

The pseudo-ternary system at 1860 °C shown in figures 2.5 contains three zirconium silicides, ZrSi, Zr<sub>2</sub>Si and Zr<sub>5</sub>Si<sub>3</sub>; boride, ZrB<sub>2</sub>; and carbide, ZrC. The FactSage database, which generated the phase diagram, does not consider the other silicide intermetallics from the Zr -Si phase diagram such as  $Zr_5Si_4$ ,  $Zr_3Si_2$  and  $Zr_3Si$ . Zr and  $ZrSi_2$  melt to form Zr-Si liquid, which then reacts with B<sub>4</sub>C leaving behind a composite of ZrB<sub>2</sub>, ZrC and Zr <sub>x</sub>Si<sub>y</sub>, given sufficient time. The stable phases ZrB <sub>2</sub> and ZrC are in equilibrium with ZrSi and Zr <sub>5</sub>Si<sub>3</sub> between 30 at% ZrSi<sub>2</sub> and 5 at% ZrSi<sub>2</sub>. The compound SiB<sub>14</sub> is formed by the reaction between B<sub>4</sub>C and SiB<sub>6</sub>.





Figure 2.3: B-C-Zr Ternary Phase Diagram at 1800°C [Outotec].









Figure 2.5: Zr-B<sub>4</sub>C-ZrSi<sub>2</sub> Pseudo-Ternary Phase Diagram at 1860°C [FactSage].



#### 2.3: Oxidation of ultra-high temperature ceramic

Transition Metal (Zr, Hf, Ti and Ta) diborides and carbides are more suitable -high temperature ceramics (UHTC) because of their oxidation for use as ultra resistance by forming scales, there by, reducing oxygen ingress [ Opeka-2004, Fahrenholtz-2007]. The oxidation resistance of borides and carbides can be increased by the addition of Si, which form a protective SiO <sub>2</sub> layer [Hinze-1975]. Researchers have reported the formation of multi -layer oxide scale upon oxidat ion of ZrB 2-SiC composite at temperatures greater than 1500 °C [ Hinze-1975, Karlsdottir -2007, Fahrenholtz-2007, Monteverde - 2007]. Up to 1200°C, the liquid SiO<sub>2</sub>-B<sub>2</sub>O<sub>3</sub> protects the composite by preventing oxygen diffusion a nd preventing scale spallation. At temperatures greater than 1200°C, the boria vaporizes from the outer borosilicate scale and completely at around 1500°C leaving behind an outer amorphous silica-rich scale with ZrO<sub>2</sub> precipitates covering a zirconia-rich scale with SiO<sub>2</sub> precipitates. This layered oxide scales are capable of extremely high temperature oxidation resistance due to the viscosity and wettability of SiO<sub>2</sub> glass layer. The diffusion of oxygen through the liquid SiO<sub>2</sub> layer is the rate-determining step and shows parabolic oxide scale growth rate. A simulated ZrO<sub>2</sub>-SiO<sub>2</sub> scale on a ZrB<sub>2</sub>-ZrC-Zr composite is shown in figure 2.6.

#### 2.3.1 Zr-Si-O Phase Diagram

From the Zr-Si-O ternary phase diagram shown in figure 2.7, the equilibrium phases, which must be present at 1680 °C, are  $ZrO_2$  (solid), SiO<sub>2</sub> (liquid) and ZrSiO<sub>4</sub>. A discrepancy exists in this phase diagram as  $ZrSiO_4$  is shown to be present even though the pseudo-binary  $ZrO_2$ -SiO<sub>2</sub> phase diagram (figure 2.8) suggests dissociation of  $ZrSiO_4$ 



the pseudo-binary  $ZrO_2$ -SiO<sub>2</sub> phase diagram (figure 2.8) suggests dissociation of  $ZrSiO_4$  at 1673 °C. The  $ZrO_2$ - $ZrSi_2$  tie line prevents other silicides from equilibrating with SiO  $_2$  and  $ZrSiO_4$ .

#### 2.3.2 ZrO<sub>2</sub>-SiO<sub>2</sub> Phase Diagram

The pseudo -binary phase diagram of ZrO  $_2$ -SiO<sub>2</sub> in figure 2 . & h o w s compound Zircon (ZrSiO<sub>4</sub>), which decomposes in solid state at 1673 °C into solids, ZrO<sub>2</sub> and SiO<sub>2</sub>. The two solid phases , ZrO<sub>2</sub> and SiQ, co-exist represented by the horizontal tie lines between 1687 °C and 1673 °C and SiO<sub>2</sub> melting temperature is 1723 °C. Eutectic reaction occurs on the SiO <sub>2</sub>-rich region at 1687 °C, but SiO <sub>2</sub> is not sol uble in ZrO<sub>2</sub>. The melting temperature of ZrO  $_2$  is 2 6 %C0and exists as monoclinic - ZrO  $_2$  at room temperature with transformation to tetragonal - ZrO<sub>2</sub> at 1205°C and the tetragonal - ZrO<sub>2</sub> transformation at 2370 °C. There is a 9% volume increase when tetragonal - ZrO<sub>2</sub> transforms to monoclinic - ZrO<sub>2</sub>. The liquidus line exists over the entire region with a miscibility gap between 2250°C and 2430°C indicated by L1 + L2.









Figure 2.7: Zr-Si-O Ternary Phase Diagram at 1680°C [Sorrell-1986].





Figure 2.8: ZrO<sub>2</sub>-SiO<sub>2</sub> Pseudo-Binary Phase Diagram [Kaiser-2008].



## **Chapter 3: RESEARCH METHODOLOGY**

#### 3.1: Sample Preparation

B<sub>4</sub>C powder (99+%, < 10 micron) and ZrSi<sub>2</sub> (99.5%, -325 mesh) supplied by Alfa Aesar was packed into a graphite crucible (0.5" OD, 1mm thick and 0.6" length) acquired from LECO. Zr slugs (99.5%, 3.175 mm diameter and 3.175 mm length ), also obtained from Alfa Aesar, and was then placed on top of the ZrSi<sub>2</sub> powder. Graphite covers were used at the top of the graphite crucibles to push back the levitating Zr -Si melt. Two different compositions of ZrSi<sub>2</sub> were used, 0.57 g and 0.8 g, with the weights of B<sub>4</sub>C (0.25 g) and Zr (1.5 g) kept constant. The 0.57 g sample corresponds to Zr -12wt%Si and 0.8 g sample corresponds to Zr-16wt%Si on the Zr-Si phase diagram. The sample setup is shown is figure 3.1.



Figure 3.1: Sample Setup.

The samples were then placed in a grap hite enclosure (Figures 3.3 and 3.4) machined from a graphite rod (2 " diameter  $\times$  17" length) acquired from American Graphite Corporation. Figure 3.2 shows the graphite enclosure insulated by zirconia



grog (-8/+20 mesh ) sourced from Zircoa. A zirconia crucible sufficiently shielded the graphite enclosure from the high magnetic fields generated by the induction furnace . GM Associates supplied the quartz reaction tube and CoorsTek, Inc supplied the zirconia crucible stabilized with  $Y_2O_3$  (35 mm diameter × 64 mm length). Pure aluminum wire (99.999%, 0.81mm diameter) procured from Alfa Aesar was rolled around the bottom part of the graphite enclosure, which oxidized to form a seal, thereby creating an inert atmosphere inside the graphite crucible. Titanium slugs and aluminum slugs were placed in the Al -Ti melt pit, as shown in figure 3.4, was used for the purpose of removing any residual oxygen left inside the graphite enclosure. The titanium slugs (99.5%, 3.175 mm diam eter and 3.175 mm length) and aluminum slugs (99.5%, 3.175 mm length) were sourced from Alfa Aesar.

#### **3.2: Experimental Procedure**

The ZrB 2-ZrC-Zr<sub>X</sub>Si<sub>Y</sub> composite was processed in a n i nduction furnace with operating frequency of 4.5 MHz with temperature controlled by an Ircon Maxline CPU<sup>TM</sup> infrared pyrometer sighting on the graphite enclosure . The induction furnace was acquired from Thermal Technology Inc. The set temperature was little more than the melting temperature of Zr at 1860 °C, but due to the exothermic reactions, temperatures inside the graphite enclosure will be in the region of 2300 °C – 2400°C [Johnson-1991]. Deoxidized helium gas was p assed through the entire setup, which is shown in figure 3.5. Helium gas was preferred over argon gas to avoid plasma formation . The purification of helium was achieved in 3 steps. First, h elium gas was passed through a column of magnesium perchlorate to remove moisture. Two subsequent steps of passing the He gas through tubes containing titanium sponge, obtained from Alfa Aesar,



column of magnesium perchlorate to remove moisture. Two subsequent steps of passing the He gas through tubes containing titanium sponge, obtained from Alfa Aesar, deoxidized the gas. The first tube with titanium sponge was mainta**70@C** atd the second tube was maintained at 800°C bringing down the oxygen potential of helium gas to  $10^{-60}$  atm before entering the reaction tube setup. The helium gas was vented out into a dibutylphilate bubble r. Diagrams of the reaction tube, reaction tube cap, cooling jacket, lower bottom reaction tube cap, and cooling jacket cap are shown from figures 3.6 - 3.10.

The experiments were successfully run by holding the induction furnace at 1860°C for 60, 120, 180, and 240 minutes with the last reacting time giving sufficient time for the entire melt to equilibrate. The temperature ramp rate was 30°C/minute from room temperature to 1000 °C and 8 °C/minute from 1000 °C to 1860 °C, which is the set temperature. At the end o f the experiment, rapid cooling was maintained to freeze the microstructure achieved at higher temperatures. Temperature calibration was achieved by placing platinum wire on the graphite enclosure, which could be seen through the sighting tube of the pyrom eter. When the platinum wire melted at its melting temperature of 1773 °C, the temperature of 1860 °C and platinum melting temperature of 1773°C.

#### 3.3: Microstructure Characterization

The processed samples were cut along its length using a Struers – Accutom 2



table saw equipped with a diamond cut -off wheel. The cross -sections were then mounted on epoxy resin supplied by Pace Technologies and prepared by grinding with 120, 240, 4 00, 600, 800, and 1000 grit paper and finished by polishing with 1 $\mu$ m diamond paste. The polished samples were rinsed with water and methanol before drying them with a blower. The microstructures of the cross -sectioned samples were analyzed with scanning electron microscope (Hitachi), optical microscope (Reichter) and X-ray diffractometer (Bruker) . T h eX-ray diffractometer was operating with an accelerating voltage of 40 kV and a beam current of 40 mA for an angle 20 of 10°-70°.







Figure 3.3: Graphite Enclosure with Graphite Crucible Sample.





Figure 3.4: Cross-section of the Graphite Enclosure.











Figure 3.8: Quartz Reaction Tube.







Figure 3.7: Cooling Jacket.





Figure 3.9: Bottom Reaction Tube Cap.



Figure 3.10: Cooling Jacket Cap.



#### Chapter 4: RESULTS

In this chapter, X -ray diffraction patterns and micrographs of th e processed composites are described. The starting compositions of the samples were Zr -12wt%Si and Zr -16wt%Si with B <sub>4</sub>C constant at 0.25 g and they were heated at the set temperature of 1860 °C for 60, 120, 180, and 240 minutes. The formation of pellet-like not possible due to the zirconium composites was levitation caused by the electromagnetic field of the induction furnace. The electromagnetic field brought about mixing of the melt at different places inside the graphite crucible leaving behind a highly heterogeneous microstructure . Description of accurate interfacial reactions, which occurred during the process, is not feasible due to the melt solidifying at different places on the graphite crucible. All samples observed showed varying porosity and grain size with greater porosity for shorter duration of reaction time . The increased porosity for shorter reaction times is due to the incomplete reactions between the free B<sub>4</sub>C and the Zr-Si melt. An example of a levitating composite is shown in figure 4.1. Visual inspection and XRD analysis of the cross -sectioned samples showed no oxides scales demonstrating the removal of the residual oxygen inside the graphite enclosure and proper sealing by the aluminum wire and the Al-Ti melt.

#### 4.1: X-Ray Diffraction

X-ray diffraction patterns for Zr-12 wt% Si samples and Zr -16 wt% Si samples heated at 1860°C for 60, 120, 180, and 240 minutes are shown in figures 4.2 to 4.9. The analysis of the diffracting spectra identified  $ZrB_2$  and ZrC in all four groups . A single - phase silicide, ZrSi is shown to exist in both compositions of the samples processed at



1860°C for all the four groups. In 120 minutes group, a Imost similar x-ray diffraction patterns were observed compared to samples annealed at 1860 °C for 60 minutes, with the exception of the appearance of another silicide,  $Zr_5Si_4$  (tetragonal crystal structure). Almost identical patterns are acquired for samples allowed to react for 180 minutes and 240 minute s. One exception is the Zr -12 wt% Si sample reacted for 240 minutes, in which peaks matching silicide,  $Zr_2Si$ , was found (figure 4.8).

#### **4.2: Microstructures**

The SEM and optical micrograph for 60 minutes as shown in figure 4.10 and 4.11 points to the ZrB  $_2$  precipitates (hexagonal crystal structure) and ZrC precipitates (face - centered cubic crystal structure) dispersed in a Zr -Si melt. The unreacted B  $_4$ C is shown on the right in the optical micrograph. ZrB  $_2$ , ZrC and Zr  $_x$ Si $_y$  precipitates surrounded by the unreacted B  $_4$ C are shown in figure 4.11. B  $_4$ C was observed in the samples reacted for 120 minutes too (figure 4.13), indicating incomplete reactions. But, micrographs for samples reacted for 180 and 240 minutes (figures 4.15 to 4.17) demonstrates complete reaction between B  $_4$ C and Zr-Si melt forming a continuous microstructure with ZrB  $_2$ , the most dominant phase.

#### 4.3: Results Summary

 $ZrB_2$  was the main phase in the matrix after reaction. ZrSi was the only silicide identified by XRD in all 4 groups.  $Zr_5Si_4$  was detected in 3 groups excluding the 60 minutes run.  $Zr_2Si$  was spotted only in the  $Zr_-16$  wt% Si sample heated at the set temperature for 240 minutes. Other silicides like  $Zr_5Si_3$ ,  $Zr_3Si$ , and  $ZrSi_2$  were not observed on the x-ray spectrum s. Micrographs for the 4 groups showed formation of  $ZrB_2$ -ZrC composite in a solidified Zr-Si melt. Large amounts of free B<sub>4</sub>C were observed



in the shorter runs of 60 minutes and 120 minutes and considerable porosity were observed in all the samples. To conclude,  $ZrB_2$  and ZrC precipitates within a metal matrix of a Zr-Si alloy were successfully developed in both sets o f compositions heated at 1860°C for 60, 120, 180, and 240 minutes



Figure 4.1: Cross-section of a processed sample showing the effect of the levitation caused by the magnetic field of the induction furnace.







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Figure 4.3: XRD diagram for Zr-16wt%Si held at 1860°C for 60 minutes.

# المنسارات



![](_page_41_Figure_1.jpeg)

![](_page_41_Picture_2.jpeg)

![](_page_42_Figure_0.jpeg)

![](_page_42_Picture_1.jpeg)

![](_page_43_Figure_0.jpeg)

![](_page_43_Figure_1.jpeg)

![](_page_44_Figure_0.jpeg)

Figure 4.7: XRD diagram for Zr-16wt%Si held at 1860°C for 180 minutes.

![](_page_44_Picture_2.jpeg)

![](_page_45_Figure_0.jpeg)

![](_page_45_Figure_1.jpeg)

![](_page_46_Figure_0.jpeg)

Figure 4.9: XRD diagram for Zr-16wt%Si held at 1860°C for 240 minutes.

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![](_page_47_Figure_0.jpeg)

Figure 4.10: SEM Micrograph of  $ZrB_2$ -ZrC precipitates surrounded by solidified Zr-Si melt and the unreacted B<sub>4</sub>C in sample held at 1860°C for 60 minutes.

![](_page_47_Picture_2.jpeg)

![](_page_48_Picture_0.jpeg)

Figure 4.11: Micrograph of  $ZrB_2$ -ZrC precipitates surrounded by solidified Zr-Si melt and the unreacted B<sub>4</sub>C in sample held at 1860°C for 60 minutes.

![](_page_48_Picture_2.jpeg)

![](_page_49_Picture_0.jpeg)

Figure 4.12: Micrograph with a closer look at the unreacted  $B_4C$  and  $ZrB_2$ -ZrC- $Zr_xSi_y$  precipitates in sample held at 1860°C for 60 minutes.

![](_page_49_Picture_2.jpeg)

![](_page_50_Figure_0.jpeg)

Figure 4.13: Micrograph of  $ZrB_2$ -ZrC- $Zr_xSi_y$  precipitates encased within solidified Zr-Si melt in a sample held at 1860°C for 120 minutes.

![](_page_50_Picture_2.jpeg)

![](_page_51_Picture_0.jpeg)

Figure 4.14: Micrograph with a closer look at the unreacted  $B_4C$  and  $ZrB_2$ -ZrC- $Zr_xSi_y$  precipitates in sample held at 1860°C for 120 minutes.

![](_page_51_Picture_2.jpeg)

![](_page_52_Figure_0.jpeg)

Figure 4.15: Micrograph of ZrB<sub>2</sub>-ZrC precipitates encased within solidified Zr-Si melt in a sample held at 1860°C for 180 minutes.

![](_page_52_Picture_2.jpeg)

![](_page_53_Picture_0.jpeg)

Figure 4.16: Micrograph of ZrB<sub>2</sub>-ZrC precipitates in a completely reacted sample held at 1860°C for 180 minutes.

![](_page_53_Picture_2.jpeg)

![](_page_54_Picture_0.jpeg)

Figure 4.17: Micrograph with ZrB<sub>2</sub>-ZrC precipitates in a completely reacted sample held at 1860°C for 240 minutes.

![](_page_54_Picture_2.jpeg)

## **Chapter 5: DISCUSSION**

#### 5.1: Oxygen Potential Reduction within the graphite Enclosure

The absence of  $ZrO_2$  and  $Al_2O_3$  peaks in the x -ray diffraction patterns shown from figure 4.2 to figure 4.9, for the 2 different compositions of samples processed for 60 to 240 minutes indicate successful reduction of the oxygen potential within the graphite enclosure by the aluminum and t itanium slugs. The removal of oxygen can be explained with the help of the Ellingham diagram, which depicts Gibbs free energy of formation with temperature. The Ellingham diagram for the o xides (figure 5.1) indicates that at 2000 °C, Y<sub>2</sub>O<sub>3</sub> is the most stable oxide, as demonstrated by the lowest free energy. For ZrO<sub>2</sub> and Al<sub>2</sub>O<sub>3</sub>, the lines intersect at 730°C, which suggests that at temperatures less than 730°C, the liquid aluminum (melting temperature of 665°C) has greater affinity for oxygen than zirconium does.

#### 5.2: Phase Relations between Zr/B<sub>4</sub>C/Si

The Zr -B<sub>4</sub>C-ZrSi<sub>2</sub> ternary phase diagram at 1900°C and 2400°C shown in figures 5.2 and 5.3, respectively, suggests the formation of solid ZrB<sub>2</sub> and ZrC with liquid for the chosen stoichiometric ratios of Zr -12wt%Si (blue line) and Zr -16wt%Si (red line). The isothermal section of the phase diagram is observed at 2400 °C also, to account for the temperature rise inside the graphite crucible due to the highly exothermic nature of the reactions. Johnson et al. [6] reported adiabatic reaction temperatures to reach around 2300 °C -2400°C during the processing of ZrB  $_2$ -ZrC-Zr composites. Three zirconium silicides, ZrSi, Zr<sub>2</sub>Si and Zr<sub>5</sub>Si<sub>3</sub> are observed in the phase

![](_page_55_Picture_5.jpeg)

diagrams. The compound SiB  $_{14}$ , formed by the reaction between B  $_4$ C and SiB  $_6$ , decomposes before 2400°C is reached and was never observed on the XRD patterns.

#### 5.3: X-Ray Diffraction

The XRD spectrums (figures 4.2 to 4.9) for the samples reacted for 60. 120, 180, and 240 minutes, indicates the formation of ZrB 2 and ZrC precipitates in a solidified Zr -Si melt. ZrSi, is the only silicide to make an appearance in XRD spectrums for all the samples. This suggests the ZrSi prevails over all other silicides to become the main silicide. There was no considerable difference observed in the phases detected for the 2 different stoichiometric ratios due its closeness on the Zr -Si phase diagram [6]. The formation of ZrSi means the reaction moved to the left of Zr <sub>3</sub>Si on the Zr -Si phase diagram shown in figure 2.1. To understand the formation of Zr <sub>5</sub>Si<sub>4</sub> in all the samples except for samples reacted for 60 minutes, Ellingham diagrams for silicides are plotted. The Gibbs free energy of f ormation for the different silicides was generated using FactSage. Table 5.1 shows the Gibbs free energy of formation at temperatures, 200 °C, 800°C, 1500 °C, 2000 °C, and 2500 °C. In the plot of  $\Delta G$  vs. temperature (figure 5.4), Zr<sub>5</sub>Si<sub>4</sub> is the most stable silicide, which explains its presence in the XRD results. Zr <sub>5</sub>Si<sub>3</sub> is the second most stable silicide, which is a discrepancy due its metastable nature at temperatures lower than 1745°C, which is not available on the FactSage database. The formation of Zr<sub>2</sub>Si in the Zr-16wt%Si sample reacted for 240 minutes is probably due to separate magnetic field mixing or kinetic problem with the reaction not proceeding to form Zr-Si or Zr<sub>5</sub>Si<sub>4</sub>

![](_page_56_Picture_3.jpeg)

#### 5.4: Microstructures

The microstructure images for the samples reacted for 60, 120, 180, and 240 minutes are shown from figures 4.10 to 4.17. The microstructures obtained are as suggested by the phase diagram with  $ZrB_2$  and ZrC precipitates dispersed in solidified liquid. There was considerable unreacted B  $_4C$  in the 60 minutes and 120 minutes samples. This is a result of insufficient time for the reactants to achieve thermo - chemical equilibria as a more continuous microstructures with little unreacted B  $_4C$  were observed in the 180 minutes and 240 minutes sample es. The formation of  $ZrB_2$  and ZrC surrounded by solidified Zr-Si melt is due to the melting of zirconium slugs to form Zr -Si melt which reacts with B  $_4C$  to form  $ZrB_2$  and ZrC. On a Zr -B-C ternary, the join representing the Zr liquid reacting with B  $_4C$  is show n in figure 2.4. Through the mass balance, the ZrC and  $ZrB_2$  are formed as necessitated by the diffusional path crossing the join at least once. The shaded areas on either side of the join must be equal.  $Zr_5Si_3$  appears in the Zr-B<sub>4</sub>C-Si ternary phase diagram but is not seen in the samples due to its metastable state at lower temperatures [Okamoto-1990].

![](_page_57_Picture_2.jpeg)

![](_page_58_Figure_0.jpeg)

Figure 5.1: Ellingham Diagram for oxides.

![](_page_58_Picture_2.jpeg)

![](_page_59_Figure_0.jpeg)

![](_page_59_Figure_1.jpeg)

![](_page_59_Picture_2.jpeg)

![](_page_60_Figure_0.jpeg)

Figure 5.3: Zr-B<sub>4</sub>C-Si Pseudo-Ternary Phase Diagram at 2400°C.

![](_page_60_Picture_2.jpeg)

Table 5.1 Gibbs free energy of formation for zirconium silicides.

Temperature °C	Zr₃Si kJ/mol	Zr <sub>2</sub> Si kJ/mol	Zr <sub>3</sub> Si <sub>2</sub> kJ/mol	Zr₅Si₄ kJ/mol	ZrSi kJ/mol	ZrSi <sub>2</sub> kJ/mol
200	-231	-223	-422.	-763	-163	-168
800	-214	-210	-395	-721	-155	-163
1500	-188	-199	-351	-648	-145	-149
2000	-156	-175	-289	-534	-124	-111

![](_page_61_Figure_2.jpeg)

Figure 5.4: Ellingham Diagram for Zirconium Silicides.

![](_page_61_Picture_4.jpeg)

## **Chapter 6: CONCLUSION**

Two compositions of stoichiometric ratios, Zr-12wt%Si and Zr-16wt%Si, were reacted with B  $_4$ C at 1860 °C f or 60 minutes, 120, 180, and 240 to determine the relationship between time and reactivity. The processed samples were characterized using an optical microscope and x-ray diffraction (XRD). Microstructures with ZrB<sub>2</sub> and ZrC precipitates surrounded by solidified Zr-Si melt were observed in all the samples as expected with ZrSi, the main phase of silicide detected. Free B<sub>4</sub>C was detected in the 60 minutes and 120 minutes due to short durat ion of reaction time. One concern was the considerable porosity observed due to the furnace's electromagnetic field, which levitated the Zr liquid, but the ZrO  $_2$ -Y<sub>2</sub>O<sub>3</sub> crucible shield decreased the levitation significantly. The Zr -Si liquid reacted completely with B  $_4$ C as observed in the 180 minutes and 240 minutes samples suggesting sufficient time for the reactants to attain phase equilibria was reached for the ultrahigh temperatures achieved.

![](_page_62_Picture_2.jpeg)

#### REFERENCES

[1] Bronson, A., Ma, Yu-Tao., Mutso, R. R., and Pingitore, N., Compatibility of refractory metal boride/oxide composites at ultrahigh temperatures. Journal of Electrochemical Society., 1992, 139(11), 3183-3196.

[2] Bronson, A. and Odegard, C., The reactive liquid processing of ceramic -metal composites. Journal of the Minerals, Metals & Materials Society, 1997, 52-54.

[3] Bronson, A., and Chessa, J., Evaluation of vaporizing rates of SiO2 and TiO2 as protective coatings for ultrahigh temperature ceramic composites. Journal of European Ceramic Society, 2008, 91(5), 1448-1452.

[4] Canel, J., Zaman, J., Bettembourg, J., Flem, M. L. and Poissonnet, S., Composite zirconium silicides through an in situ process. International Journal of Applied Ceramic Technology., 2006, 3(1), 23-31.

[5] FactSage, Company: Thermfact/ CRCT-GTT, File version 6.1.

[6] Fahrenholtz, W. G., Reactive Processing in Ceramic -Based Systems. International Journal of Applied Ceramic Technology, 2006, 3(1), 1-12.

[7] Fahrenholtz, W. G., Hilmas, G. E., Refractory Diborides of Zirconium and Hafnium. J. American Ceramic Society, 2007, 90(5), 1347-1364.

[8] Fahrenholtz, W. G., Rezaie, A., and Hilmas, G. E., Evolution of structure during the oxidation of zirconium diboride -silicon carbide in air up to 1500 °C. Journal of American Ceramic Society, 2007, 27, 2495-2501.

![](_page_63_Picture_9.jpeg)

[9] Hinze, J. W., Tripp, W. C. and Graham, H. C., The high -temperature oxidation behavior of a HfB  $_2+20$  v/o SiC composite. Journal of Electrochemical Society, 1975, 122(9), 1249-1254.

[10] Johnson, W. B., Nagalberg, A. S. and Breval, E., Kinetics of formation of a platelet reinforced ceramic composite prepared by a directed reaction of zirconium with boron carbide. Journal of American Ceramic Society, 1991, 74(9), 2093-2101.

[11] Kaiser, A., Lobert, M., and Telle, R, Thermal stability of zircon (ZrSiO <sub>4</sub>). Journal of European Ceramic Society, 2008, 28, 2199-2211.

[12] Karlsdottir, S. N., and Halloran, J. W., Rapid oxidation characterization of ultra -high temperature ceramics, Journal of American Ceramic Society, 2007, 92(2), 481-486.

[13] Levine, S. R., Opila, E. J., Halbig, M. C., Kiser, J. D., Singh, M., and Salem, J.

A., Evaluation of ultra -high temperature ceramics for aeropropulsi on use. Journal of European Ceramic Society, 2002, 22, 2757-2767.

[14] Lu, P. and Du, T. B. and Loehman, R. E., Ewsuk, K. G. and Fahrenholtz, W. G., Interfacial microstructure formed by reactive metal penetration of AI into mullite. Journal of Materials Research, 1999, 14(9), 3530-3537.

[15] Monteverde, F., and Savino, R., Stability of ultra -high-temperature ZrB2 -SiC ceramics under simulated atmospheric re -entry conditions. Journal of European Ceramic Society, 2007, 27, 4797-4805.

[16] Okamoto, H., the Si-Zr System. ASM International, 1990, 11(5), 513-519.

[17] Okamoto, H., B -Zr (Boron -Zirconium). Journal of Phase Equilibria, 1993, 14(2), 261-262.

![](_page_64_Picture_10.jpeg)

[18] Okamoto, H., C -Zr (Carbon -Zirconium). Journal of Phase Equilibria, 1996, 17(2),162.

[19] Opeka, M. M., Talmy, I. G. and Zaykoski, J. A., Oxidation-based materials selection for 2000°C+ hypersonic aerosurfaces: theoretical considerations and historical experience. Journal of Materials Science, 2004, 39(19), 5887-5904.

[20] Outotec

[21] Petla, H., Renova, E. P., Bronson, A., Chessa , J. F., and Maheswar aiah, B. M., A computational analysis of a ZrO <sub>2</sub>-SiO<sub>2</sub> scale for a ZrB <sub>2</sub>-ZrC-Zr ultrahigh temperature ceramic composite system. Journal of European Ceramic Society, 2010.

[22] Sorrell, C. C., McCartney, E. R., Phase equilibrium in the system zirconium-siliconoxygen. In: Proceedings of the 12<sup>th</sup> Australian Ceramics Conference, 1986.

[23] Tomsia, A. P., Saiz, E., Foppiano, S., MoberlyChan, W., Synthesis and processing of ceramic-metal composites by reactive metal penetration. Composites: Part A, 1999, 30, 399-403.

![](_page_65_Picture_6.jpeg)

## **CURRICULUM VITA**

Nischel B. Maheswaraiah was born on July 2, 1985, in Shimoga, Karnataka, India. The second son of Maheswaraiah Shivanna and Bhagyavathi Basappa , he graduated with Mathematics and Science Degree in 2003 from Karnataka Lingayat Education College (Bangalore, India). He received his Bachelor's degree in Mechanical Engineering from People's Education Society Institute of Technology (P.E.S.I.T) in 2007. He finished his Master's in Mechanical Engineering in 2010 at University of Texas at El Paso, El Paso, Texas.

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![](_page_66_Picture_6.jpeg)